P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 12	0.156 at V_{GS} = - 4.5 V	1.18	6.7 nC
	0.190 at V_{GS} = - 2.5V	1.07	
	0.245 at V_{GS} = - 1.8V	0.49	

FEATURES

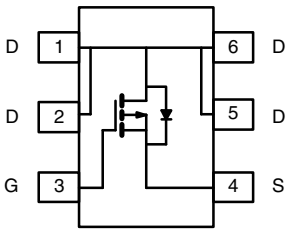
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE

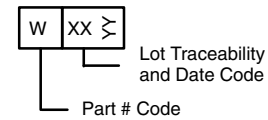
APPLICATIONS

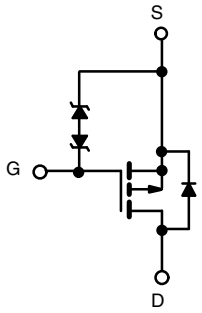
- Load Switch for Portable Devices

SC-89 (3-LEADS)



Top View





P-Channel MOSFET

Ordering Information: Si1065X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 12	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current (T_J = 150 °C)	T_A = 25 °C	I_D	- 1.18[b, c]	A
	T_A = 70 °C		- 0.94[b, c]	
Pulsed Drain Current		I_{DM}	- 8	
Continuous Source-Drain Diode Current	T_A = 25 °C	I_S	- 0.2[b, c]	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	0.236[b, c]	W
	T_A = 70 °C		0.151[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a, b]	t ≤ 5 s	R_{thJA}	440	530	°C/W
	Steady State State		540	650	

Notes:
a. Maximum under steady state conditions is 650 °C/W.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.

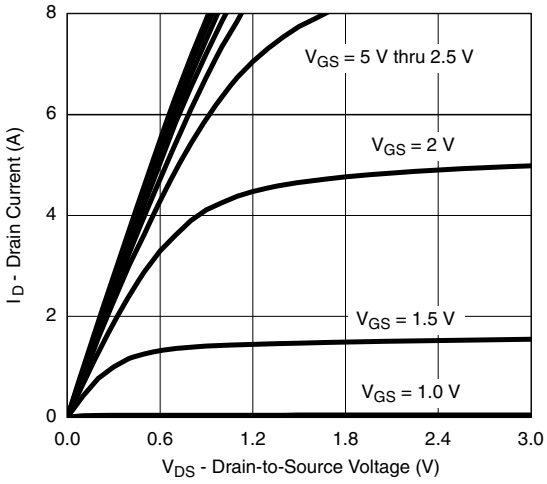
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 12			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 8.47		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.33		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.45		- 0.95	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 12 V, V_{GS} = 0 V			- 1	nA
		V_{DS} = - 12 V, V_{GS} = 0 V, T_J = 85 °C			- 10	µA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = ≥ 5 V, V_{GS} = - 4.5 V	- 8			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 1.18 A		0.108	0.156	Ω
		V_{GS} = - 2.5 V, I_D = - 1.07 A		0.131	0.190	
		V_{GS} = - 1.8 V, I_D = - 0.49 A		0.158	0.245	
Forward Transconductance	g_{fs}	V_{DS} = - 6 V, I_D = - 1.18 A		5.18		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 6 V, V_{GS} = 0 V, f = 1 MHz		480		pF
Output Capacitance	C_{oss}			190		
Reverse Transfer Capacitance	C_{rss}			145		
Total Gate Charge	Q_g	V_{DS} = - 6 V, V_{GS} = - 5 V, I_D = - 1.18 A		7.2	10.8	nC
		V_{DS} = - 6 V, V_{GS} = - 4.5 V, I_D = - 1.18		6.7	10.1	
Gate-Source Charge	Q_{gs}			0.84		
Gate-Drain Charge	Q_{gd}			2.7		
Gate Resistance	R_g	f = 1 MHz		10	15	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 6 V, R_L = 6.32 Ω I_D ≅ - 0.95 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		13	19.5	ns
Rise Time	t_r			27	40.5	
Turn-Off DelayTime	$t_{d(off)}$			45	67.5	
Fall Time	t_f			27	40.5	
Drain-Source Body Diode Characteristics						
Pulse Diode Forward Current[a]	I_{SM}				8	A
Body Diode Voltage	V_{SD}	I_S = - 0.63 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 0.7 A, dI/dt = 100 A/µs		29.2	44	nC
Body Diode Reverse Recovery Charge	Q_{rr}			10.22	15.3	ns
Reverse Recovery Fall Time	t_a			13.7		
Reverse Recovery Rise Time	t_b			15.5		

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

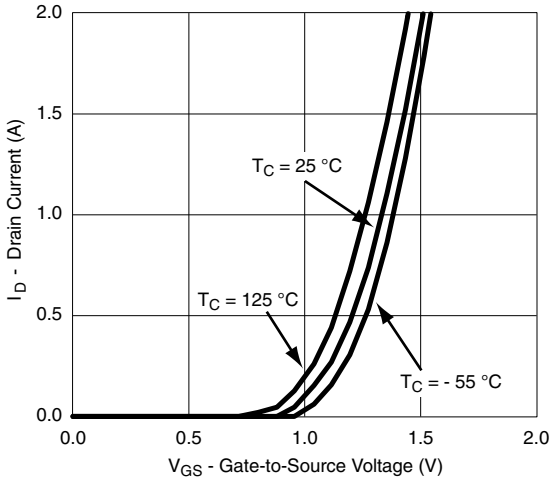
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

For technical questions, contact: pmostechsupport@vishay.com
Document Number: 74320
S12-1619-Rev. D, 09-Jul-12

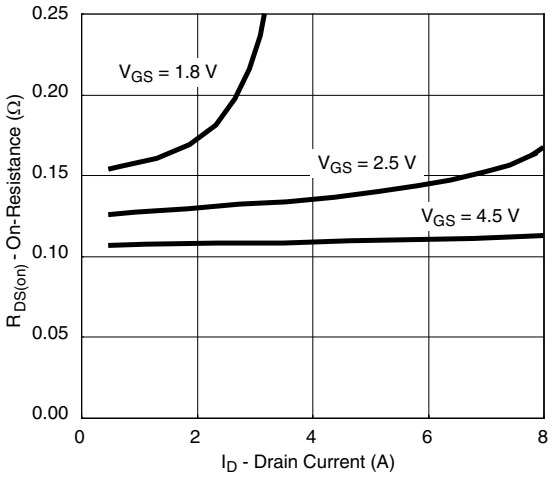
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



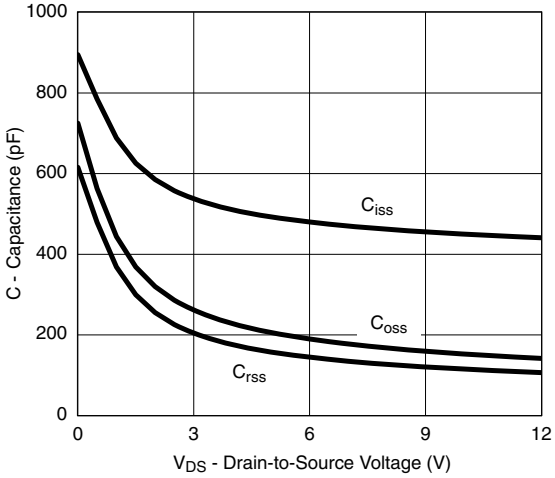
Output Characteristics



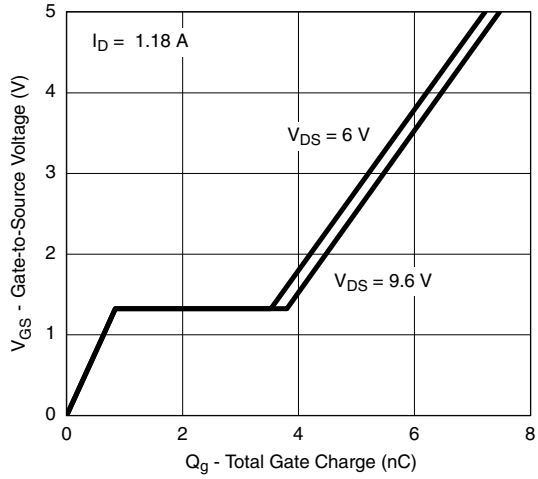
Transfer Characteristics Curves vs. Temp.



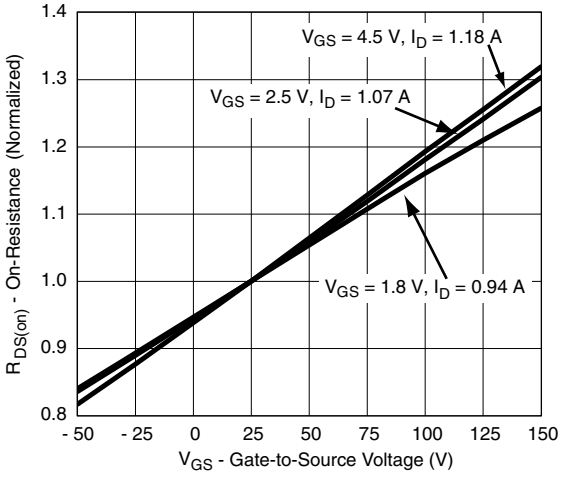
On-Resistance vs. Drain Current



Capacitance

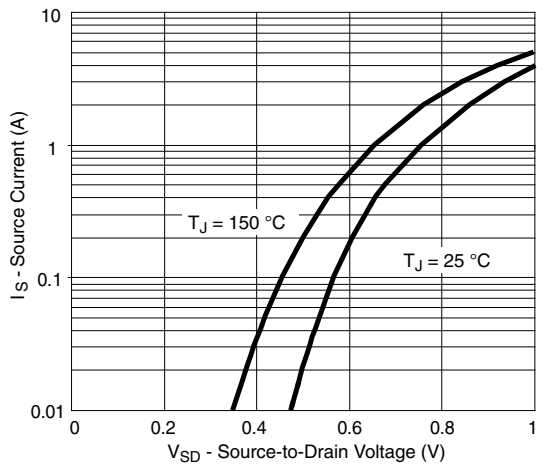


Gate Charge

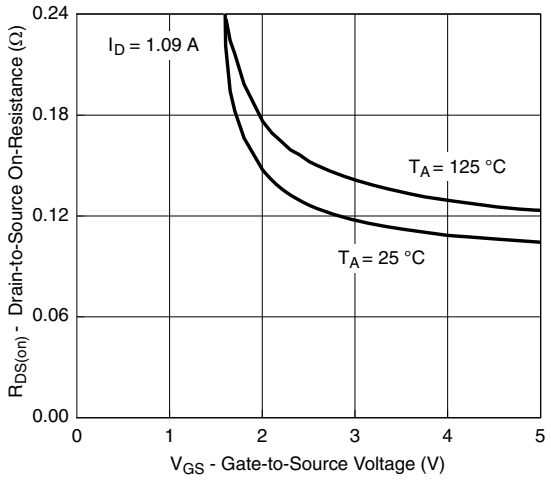


On-Resistance vs. Junction Temperature

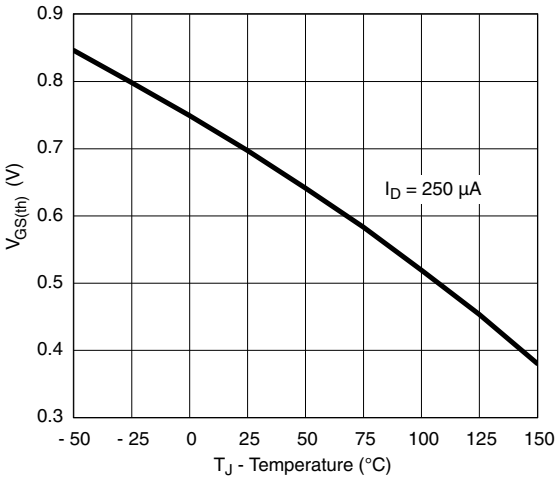
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



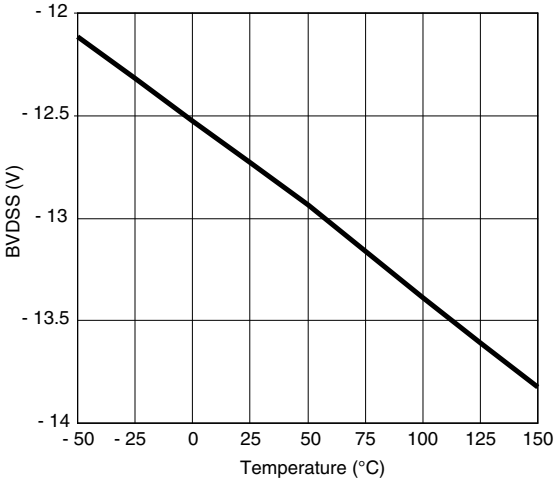
Source-Drain Diode Forward Voltage



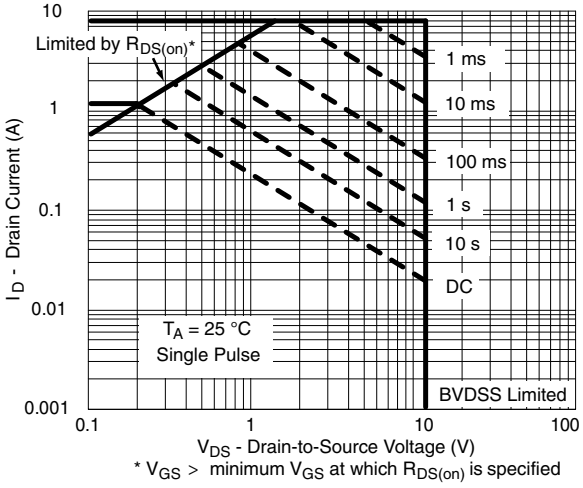
$R_{DS(on)}$ vs. V_{GS} vs. Temperature



Threshold Voltage



BVDSS vs. Temparture



Safe Operating Area, Junction-to-Ambient

For technical questions, contact: pmostechsupport@vishay.com

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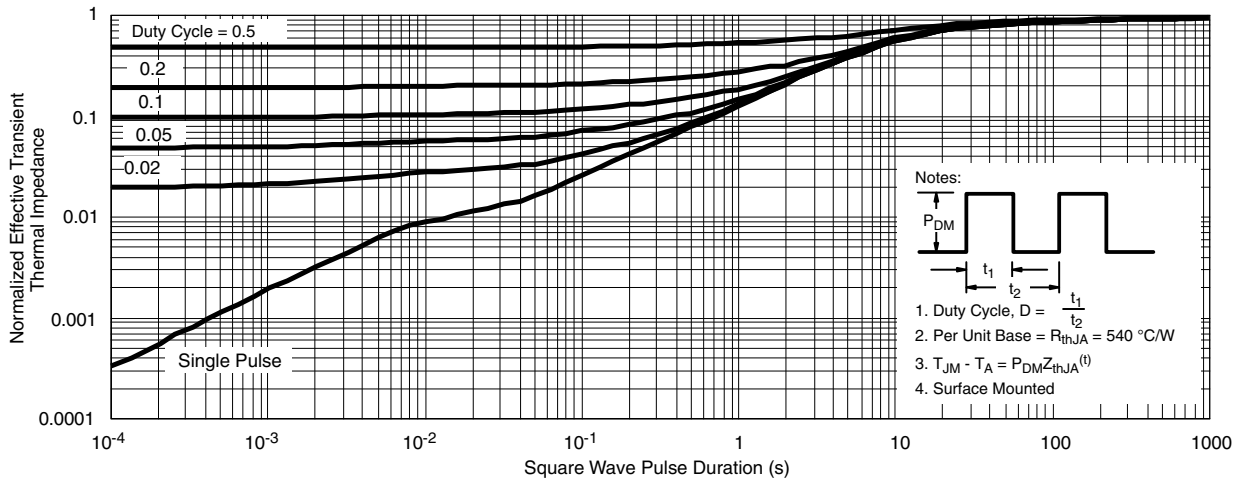
S12-1619-Rev. D, 09-Jul-12

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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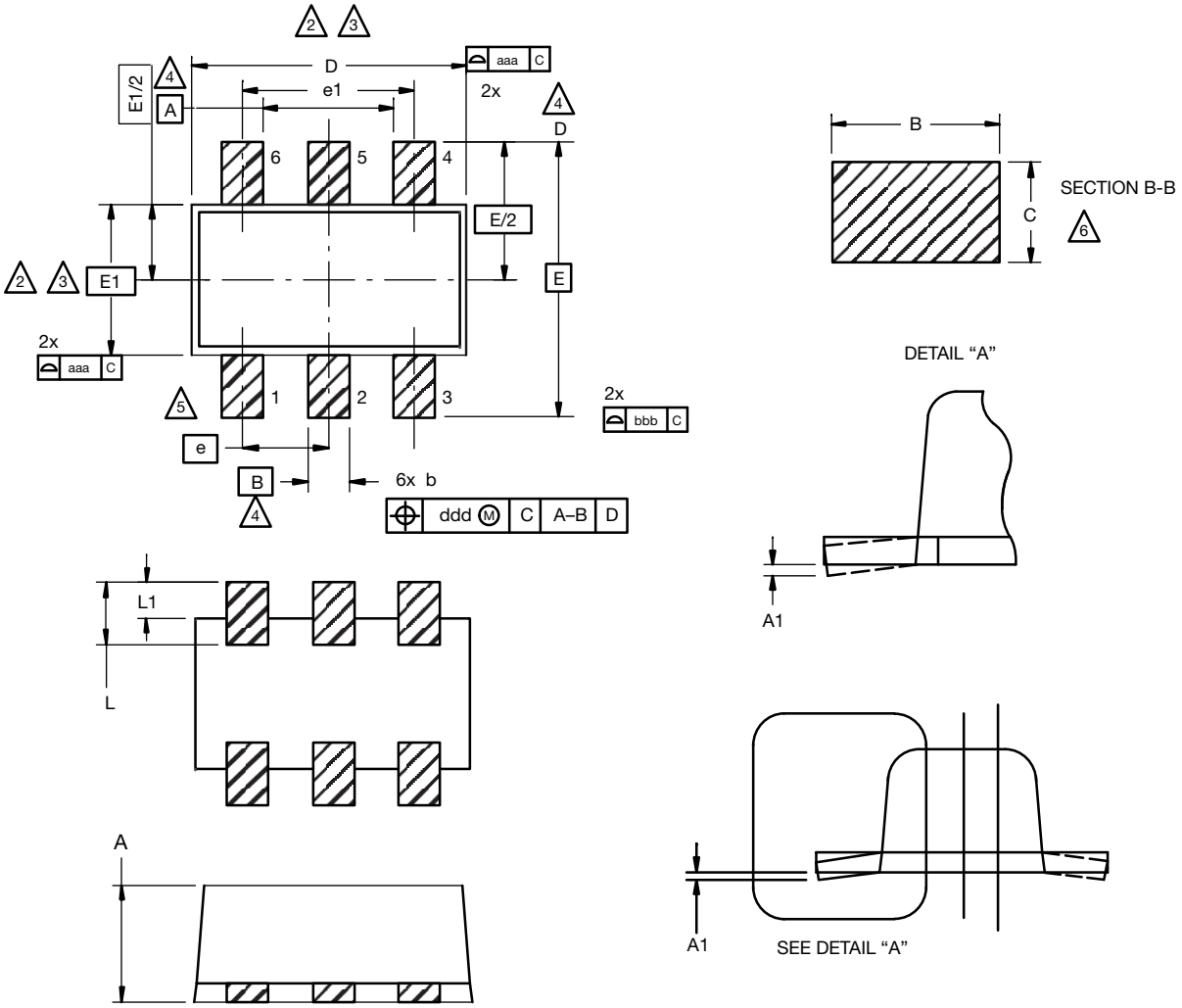
SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

2. Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

3. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

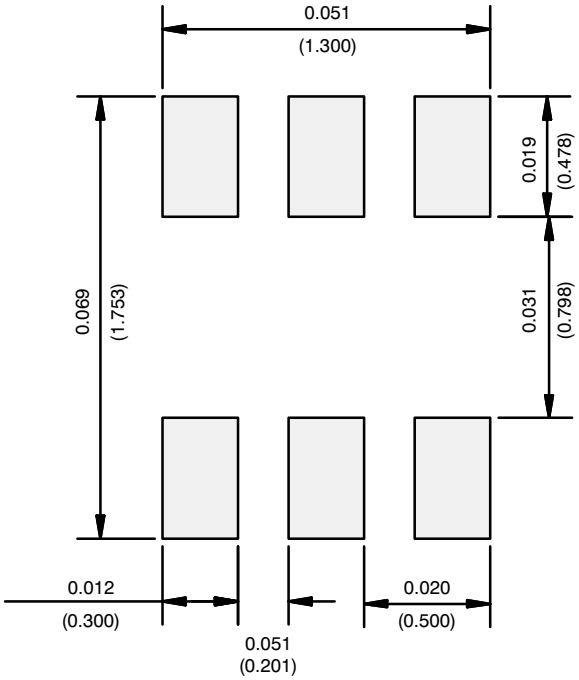
4. Datums A, B and D to be determined 0.10 mm from the lead tip.

5. Terminal numbers are shown for reference only.

6. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30
C14-0439-Rev. C, 11-Aug-14 DWG: 5880			

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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